

## **General Description**

The AAT8303 is a low threshold P-channel MOS-FET designed for the battery, cell phone, and PDA markets. Using AnalogicTech's proprietary ultrahigh-density trench technology and space-saving, small-outline, J-lead package, performance superior to that normally found in a larger footprint has been squeezed into the area of a TSOPJW-8 package.

## **Applications**

- Battery Packs
- Battery-Powered Portable Equipment
- Cellular and Cordless Telephones
- Load Switches

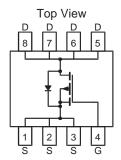
### **Absolute Maximum Ratings**

 $T_A = 25$ °C, unless otherwise noted.

### **Features**

- Drain-Source Voltage (max): -20V
- Continuous Drain Current¹ (max):
  - -10A @ 25°C
- Low On-Resistance:
  - 14mΩ @ V<sub>GS</sub> = -4.5V
  - 24mΩ @ V<sub>GS</sub> = -2.5V

### **TSOPJW-8 Package**



Symbol	Description	Value	Units		
V <sub>DS</sub>	Drain-Source Voltage		-20	V	
$V_{GS}$	Gate-Source Voltage		±12		
I <sub>D</sub>	Continuous Drain Current @ T <sub>J</sub> = 150°C¹	$T_A = 25$ °C	±10		
		T <sub>A</sub> = 70°C	±8	A	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>		±48	A	
I <sub>S</sub>	Continuous Source Current (Source-Drain Diode) <sup>1</sup>	-2.3			
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C		
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C		

### Thermal Characteristics<sup>1</sup>

Symbol	Description		Тур	Max	Units	
$R_{ heta JA}$	Junction-to-Ambient Steady State		86	105	°C/W	
$R_{\theta JA2}$	Junction-to-Ambient t<5 Seconds		44	54	°C/W	
$R_{\theta JF}$	Junction-to-Foot		27	32	°C/W	
P <sub>D</sub>	Maximum Power Dissipation	T <sub>A</sub> = 25°C		2.3	W	
		T <sub>A</sub> = 70°C		1.5	VV	

<sup>1.</sup> Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications.  $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$  where the foot thermal reference is defined as the normal solder mounting surface of the device's leads.  $R_{\theta JF}$  is guaranteed by design; however,  $R_{\theta CA}$  is determined by the PCB design. Actual maximum continuous current is limited by the application's design.



### **Electrical Characteristics**

 $T_J = 25$ °C, unless otherwise noted.

Symbol	Description	Conditions	Min	Тур	Max	Units	
DC Chara	DC Characteristics						
BV <sub>DSS</sub>	Drain-Source Breakdown	$V_{GS} = 0V, I_D = -250\mu A$	-20			V	
	Voltage						
R <sub>DS(ON)</sub>	Drain-Source On-Resistance <sup>1</sup>	$V_{GS} = -4.5V, I_{D} = -10A$		11	14	mΩ	
		$V_{GS} = -2.5V, I_D = -7.6A$		18	24	11152	
$I_{D(ON)}$	On-State Drain Current <sup>1</sup>	$V_{GS} = -4.5V$ , $V_{DS} = -5V$ (pulsed)	-48			Α	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = -250\mu A$	-0.6			V	
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$			±100	nA	
	Drain Source Leakage Current	$V_{GS} = 0V$ , $V_{DS} = -20V$			-1	μΑ	
I <sub>DSS</sub>	Diam Source Leakage Current	$V_{GS} = 0V, V_{DS} = -16V, T_{J} = 70^{\circ}C^{2}$			-5	μΛ	
$g_{fs}$	Forward Transconductance <sup>1</sup>	$V_{DS} = -5V, I_{D} = -10A$		31		S	
Dynamic	Characteristics <sup>2</sup>						
$Q_{G}$	Total Gate Charge	$V_{DS} = -10V, R_D = 1.0\Omega, V_{GS} = -4.5V$		36			
$Q_{GS}$	Gate-Source Charge	$V_{DS} = -10V$ , $R_D = 1.0\Omega$ , $V_{GS} = -4.5V$		5		nC	
$Q_{GD}$	Gate-Drain Charge	$V_{DS} = -10V, R_D = 1.0\Omega, V_{GS} = -4.5V$		13			
t <sub>D(ON)</sub>	Turn-On Delay	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $R_{D} = 1.0\Omega$ , $R_{G} = 6\Omega$		10			
$t_R$	Turn-On Rise Time	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $R_{D} = 1.0\Omega$ , $R_{G} = 6\Omega$		72		ns	
t <sub>D(OFF)</sub>	Turn-Off Delay	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $R_{D} = 1.0\Omega$ , $R_{G} = 6\Omega$		78		115	
$t_{F}$	Turn-Off Fall Time	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $R_{D} = 1.0\Omega$ , $R_{G} = 6\Omega$		108			
Source-Drain Diode Characteristics							
V <sub>SD</sub>	Source-Drain Forward	V <sub>GS</sub> = 0, I <sub>S</sub> = -10A			-1.1	V	
	Voltage <sup>1</sup>						
$I_S$	Continuous Diode Current <sup>3</sup>				-2.3	Α	

<sup>1.</sup> Pulse test: Pulse Width = 300µs.

<sup>2.</sup> Guaranteed by design. Not subject to production testing.

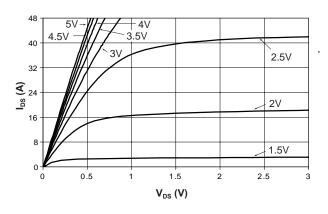
<sup>3.</sup> Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications.  $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$  where the foot thermal reference is defined as the normal solder mounting surface of the device's leads.  $R_{\theta JF}$  is guaranteed by design; however,  $R_{\theta CA}$  is determined by the PCB design. Actual maximum continuous current is limited by the application's design.



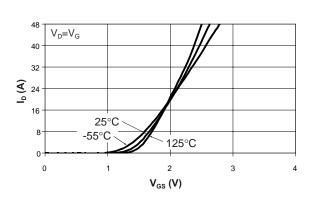
# **Typical Characteristics**

 $T_{\rm J} = 25^{\circ}$ C, unless otherwise noted.

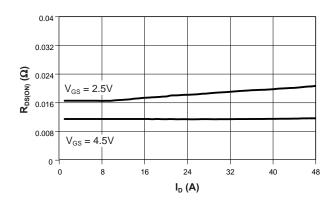
#### **Output Characteristics**



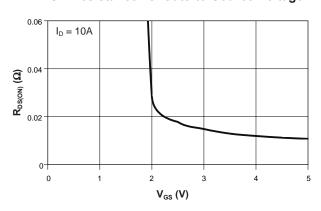
#### **Transfer Characteristics**



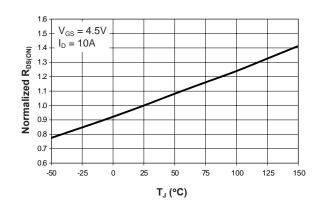
#### **On-Resistance vs. Drain Current**



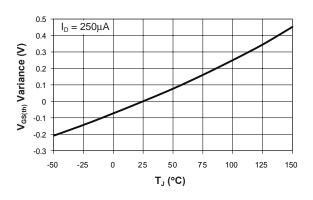
On-Resistance vs. Gate-to-Source Voltage



### On-Resistance vs. Junction Temperature



**Threshold Voltage** 

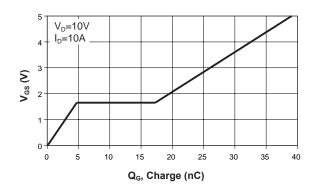




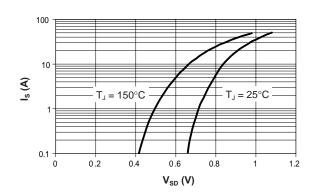
## **Typical Characteristics**

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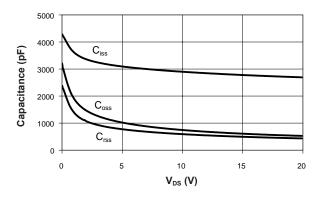
### **Gate Charge**



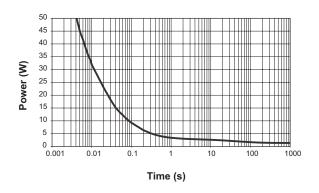
#### **Source-Drain Diode Forward Voltage**



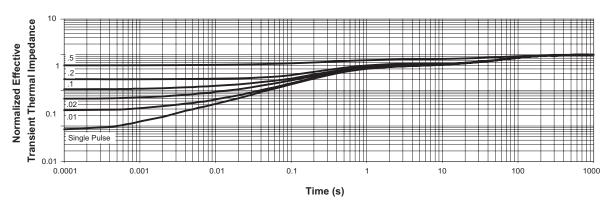
Capacitance



Single Pulse Power, Junction to Ambient



**Transient Thermal Response, Junction to Ambient** 



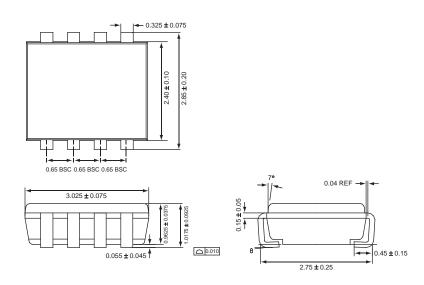


# **Ordering Information**

Package	Marking <sup>1</sup>	Part Number (Tape and Reel) <sup>2</sup>
TSOPJW-8	JXXYY	AAT8303ITS-T1

# **Package Information**

### TSOPJW-8



All dimensions in millimeters.

<sup>1.</sup> XYY = assembly and date code.

<sup>2.</sup> Sample stock is generally held on part numbers listed in **BOLD**.



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